

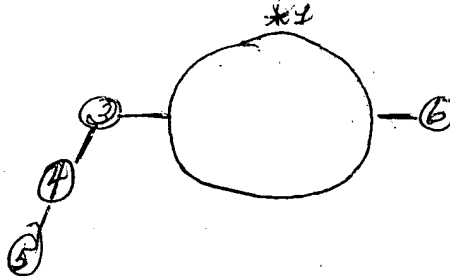
506, 534
20/10/2000

Examiner's Notes

- s (clean?) (a) steps or clean? (10a) steps?
- s (reduce? or lower? or decrease? or diminish?) (10a) (diffusion or diffusion (a) height)
- s (silicon) (a) single (u) crystal? or mono (u) crystal?
- s (RTA)
- s (thermal) (a) process?
- s (anneal?)
- s (hydrogen)
- s (temperature)

112/2 Bej

86,
Claim 3, lines 15, "... silicon-type point defect..." (Cite case law)
Claim 3, lines 6, 17, "... vacancy-type point defect..." (Cite case law)



Motivation: In order to provide a method for manufacturing a di-
single-crystal layer of which surface quality is improved & a di-
single-crystal layer is manufactured.

8,081) [51, 24 are]

2) [Crystallization apparatus]

App
II

3) [422]

4) [245, 1]

5) [5 25 - 64 are]

6) [A utd for crystallizing a molecule (S) ...]

MD
II

7) [117]

8) [86]